ABSTRACT

[Abstract of the Disclosure]

The present invention generally relates to a bitline structure of a semiconductor device having a stud type capping layer and a method of fabricating the same for obtaining process margins and reducing parasitic capacitance.

The semiconductor device of the present invention comprises: an insulating film formed on a semiconductor substrate, and having bitline contacts and groove-type bitline patterns; bitlines formed in a portion of the bitline contacts and the bitline patterns, and surrounded by the insulating film; and a bitline capping layer formed in the bitlines of the bitline patterns and the insulating film, to be protruded than the insulating film, and whose protruded part is wider than width of the bitlines.

[Representative Drawing]

FIG. 5h